NSN 5962-01-420-7499

Memory Microcircuit - Page 1 of 2

Test Data Document:



View Online at https://aerobasegroup.com/nsn/5962-01-420-7499

Body Length:
1.060 inches
Body Width:
Between 0.220 inches and 0.320 inches
Body Height:
0.185 inches
Maximum Power Dissipation Rating:
2.0 milliwatts
Operating Tempurature Range:
-55.0/+125.0 degrees celsius
Storage Tempurature Range:
-65.0/+150.0 degrees celsius
End Application:
Pacer dawn
Features Provided:
Monolithic and bipolar and programmable and electrostatic sensitive
Inclosure Material:
Ceramic
Inclosure Configuration:
Dual-in-line
Output Logic Form:
Transistor-transistor logic
Input Circuit Pattern:
16 input
Criticality Code Justification:
Cbbl
Case Outline Source And Designator:
D-8 mil-m-38510
Terminal Surface Treatment:
Solder
Product Name:
Program instruction (pal 16l8a)
Voltage Rating And Type Per Characteristic:
12.0 volts power source
Time Rating Per Chacteristic:
30.00 seconds propagation delay time, low to high level output and 30.00 nanoseconds propagation delay time, high to low level output
Memory Device Type:
Pal
Special Features:
Altered item, made from device m38510/50401brx, cage 81349, microcircuits, digital, bipolar programmable logic, monolithic silicon

81349-mil-m-38510 specification (includes engineering type bulletins, brochures, etc., that reflect specification type data in specification format; excludes commercial catalogs, industry directories, and similar trade publications, reflecting general type data on certain environmental and performance requirements and test conditions that are shown as "typical", "average", "", etc.).

NSN 5962-01-420-7499

Memory Microcircuit - Page 2 of 2



Terminal Type And Quantity:
20 printed circuit
Specification Data:
81349-mil-m-38510/504 government specification
Shelf Life:
N/a
Unit Of Measure:
Demilitarization:
No

Fiig: A458a0